

VOL. 2, NO. 12, 2013



**ECS JOURNAL OF SOLID STATE
SCIENCE AND TECHNOLOGY**



Table of Contents

Carbon Nanostructures and Devices

- Electrocatalytic Activity toward Oxygen Reduction of RuS_xN_y Catalysts Supported on Different Nanostructured Carbon Carriers**
Anna Dobrzyniecka, Pawel J. Kulesza M61

Dielectric Science and Materials

- Gap Filling Model of O₃-Tetraethylorthosilicate Film Formed on an Underlying Layer Pretreated with Organic Solvent**
Nobuyoshi Sato, Yukihiko Shimogaki N237

- Defects and Transport in Acceptor Doped La₂WO₆ and Nd_{1.2}Lu_{0.8}WO₆**
Camilla K. Vigen, Jie Pan, Reidar Haugrud N243

Electronic Materials and Processing

- Oxygen Plasma and Humidity Dependent Surface Analysis of Silicon, Silicon Dioxide and Glass for Direct Wafer Bonding**
A. U. Alam, M. M. R. Howlader, M. J. Deen P515

- Improvement of Capacitance Equivalent Thickness, Leakage Current, and Interfacial State Density Based on Crystallized High-K Dielectrics/Nitrided Buffer Layer Gate Stacks**
*Jih-Jie Huang, Li-Tien Huang, Meng-Chen Tsai,
 Min-Hung Lee, Miin-Jang Chen P524*

- Effective Capacitance Area for Pseudo-MOSFET Characterization of Bare SOI Wafers by Split-C(V) Measurements**
*Cristina Fernandez, Noel Rodriguez, Akiko Ohata,
 Francisco Gamiz, Sorin Cristoloveanu P529*

- Physical and Electrical Properties of Thin Doped Silicon Films Obtained by Low Temperature Smart Cut and Solid Phase Epitaxy**
*Gweltaz Gaudin, William Van Den Daele,
 Nicholas Chartrain, Gregory Riou, Christelle Veytizou,
 Ionut Radu, Sorin Cristoloveanu P534*

Luminescence and Display Materials, Devices, and Processing

- Effect of Barrier Growth Temperature on the Material Properties of InGaN/GaN Multiple Quantum Well Structures**
Y. Li, D. P. Byrnes, E. B. Stokes R267